

Yonenaga, I; Sakurai, M; Sluiter, MHF; Kawazoe, Y

*Local atomic structure in Czochralski-grown Ge<sub>1-x</sub>Si<sub>x</sub> bulk alloys*

Appl. Surf. Sci. 224 (2004) 193 – 196

04-IMR0161

Rodriguez, A; Bracht, H; Yonenaga, I

*Impact of high B concentrations and high dislocation densities on Au diffusion in Si*

J. Appl. Phys. 95 (2004) 7841 – 7849

04-IMR0162

Setiawan, A; Vashaei, Z; Cho, MW; Yao, T; Kato, H; Sano, M; Miyamoto, K; Yonenaga, I; Ko, HJ

*Characteristics of dislocations in ZnO layers grown by plasma-assisted molecular beam epitaxy under different Zn/O flux ratios*

J. Appl. Phys. 96 (2004) 3763 – 3768

04-IMR0163

Mchedlidze, T; Suezawa, M

*An iron-phosphorus pair in silicon*

J. Phys.-Condes. Matter 16 (2004) L79 – L84

04-IMR0164

Hayashi, K; Takahashi, Y; Yonenaga, I; Matsubara, E

*X-ray fluorescence holography study on Si<sub>1-x</sub>Gex single crystal*

Mater. Trans. 45 (2004) 1994 – 1997

04-IMR0165

Tokuyama, Y; Suezawa, M; Fukata, N; Taishi, T; Hoshikawa, K

*Occupation site change of self-interstitials and group-III acceptors in Si crystals: Dopant dependence of the Watkins replacement efficiency*

Phys. Rev. B 69 (2004) Art. No. 125217 –

04-IMR0166

Beraud, A; Kulda, J; Yonenaga, I; Foret, M; Salce, B; Courtens, E

*Disorder-induced broadening of transverse acoustic phonons in Si<sub>x</sub>Ge<sub>1-x</sub> mixed crystals*

Physica B 350 (2004) 254 – 257

04-IMR0167

Mchedlidze, T; Suezawa, M

*Influence of hydrogen on the formation of interstitial agglomerates in silicon*

Solid State Phenomena 95–96 (2004) 129 – 134

04-IMR0168

Yonenaga, I

*Dislocation-impurity interaction in silicon*

Solid State Phenomena 95–96 (2004) 423 – 432

04-IMR0169